

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4408	(peripher\$4 near3 (region area)) with memory	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 13:55
L2	2116	1 and polysilicon	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 12:06
L3	541	2 and (isolator shallow adj trench 'sti')	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 12:14
L4	159	3 and ((isolator shallow adj trench 'sti') with insulat\$4)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 12:08
L5	109	4 and dielectric	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 12:09
L6	104	5 and mask\$4	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 12:09
L8	1	7 and (mask\$4 with dish\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 12:22
L9	0	"insertion of dummy trenches to avoid silicon damage".ti.	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 12:23
L10	0	insertion adj of adj dummy adj trenches .ti.	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 12:23
L11	2	dummy adj trenches .ti.	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 12:24
L12	0	polygate adj process.ti.	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 12:24
L13	0	polygate adj process.ti.	US-PGPU B; USPAT	OR	ON	2004/11/10 13:45
L14	2393	SELF ADJ ALIGNED.TI.	US-PGPU B; USPAT	OR	ON	2004/11/10 13:46
L15	0	SELF ADJ "ALIGNED.TI.14" AND WANG	US-PGPU B; USPAT	OR	ON	2004/11/10 13:46

L17	0	15 AND YANG	US-PGPU B; USPAT	OR	ON	2004/11/10 13:47
L18	0	15 AND KIM	US-PGPU B; USPAT	OR	ON	2004/11/10 13:47
L19	0	15 AND POLYGATE	US-PGPU B; USPAT	OR	ON	2004/11/10 13:47
L20	5	"6362049"	US-PGPU B; USPAT	OR	ON	2004/11/10 13:51
L21	6977	(peripher\$4 active memory near3 (region area)) with ('sti' shallow adj trench isolator 'locos' 'fox')	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 15:13
L22	4043	21 and polysilicon	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 14:00
L23	1458	21 and (polysilicon with mask\$4)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 14:00
L24	47342	"24" and (remov\$3 with mask\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 15:12
L25	1039	23 and (remov\$3 with mask\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 15:12
L26	945	25 and (peripher\$4 active near3 (region area)) with ('sti' shallow adj trench isolator 'locos' 'fox')	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 15:23
L28	5	26 and (mask\$3 with dish\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 15:18
L29	414	(peripher\$4 near3 (region area)) with ('sti' shallow adj trench isolator 'locos' 'fox')	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 15:24
L30	126	29 and floating	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 15:24
L31	89	30 and (polysilicon near3 layer)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 15:25
L32	75	31 and (polysilicon with etch\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 15:25

L33	62	32 and (mask\$4 with etch\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 15:49
L34	42	33 and polysilicon with mask	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 15:50
L35	1	34 and dish\$3	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 15:51
L36	1035	(polysilicon with mask\$3) with (((peripher\$3 active core) near3 (region area))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 15:55
L37	32	(polysilicon with mask\$3) with (((peripher\$3 active core) near3 (region area)) with ('sti' isolator 'foc' 'locos'))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 16:01
L38	219	((polysilicon nitride) with mask\$3) with (((peripher\$3 active core) near3 (region area)) with ('sti' isolator 'foc' 'locos'))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 16:03
L39	31	((polysilicon nitride) with protect\$3) with (((peripher\$3 active core) near3 (region area)) with ('sti' isolator 'foc' 'locos'))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 16:02
L40	10	38 and ('cmp' (chemical adj mechanical adj posh\$3)) with polysilicon	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 16:07
L41	105	((peripher\$3 meory active) near3 (region area)) with ((self adj aligned) near3 (floating adj gate))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 16:09
L42	81	41 and ('sti' isolator 'fox' 'locos')	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 16:11
L43	81	42 and (dielectric insulat\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 16:12
L44	51	43 and (polysilicon (silicon adj nitride)) with ((protect\$3 mask\$4) near4 layer)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 16:14

L45	51	44 and ('cmp' remov\$3 polish\$3 planar\$6) with (polysilicon silicon adj nitride (protect\$3 mask\$4) near4 layer)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/10 16:17
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